

MBR1045L(F,B,H)CT thru MBR10200L(F,B,H)CT

10A Schottky Barrier Rectifier

FEATURE

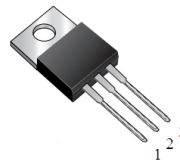
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High ESD capability
- High temperature soldering guaranteed:
260°C/10s/0.25"(6.35mm) from case

MECHANICAL DATA

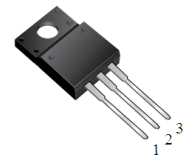
- Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy
- Mounting position: any

TYPICAL APPLICATIONS

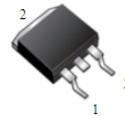
For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters and polarity protection application.



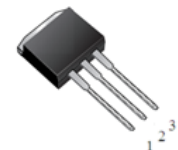
TO-220AB
MBR10XXLCT



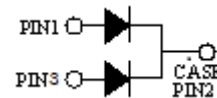
ITO-220AB
MBR10XXL^FCT



TO-262
MBR10XXL^BCT



TO-262
MBR10XXL^HCT



Ratings at 25°C ambient temperature unless otherwise specified, Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

MAXIMUM RATINGS

Parameter	Symbol	MBR1045 LCT	MBR1060 LCT	MBR10100 LCT	MBR10150 LCT	MBR10200 LCT	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	45	60	100	150	200	V
Maximum RMS Voltage	V_{RMS}	32	42	70	105	140	V
Maximum DC Blocking Voltage	V_{DC}						V
Maximum Average Forward Rectified Current at $T_C=90^\circ\text{C}$	total device	10.0					A
	per diode	5.0					
Peak Forward Surge Current 8.3ms Single Half sine-wave superimposed on rate load per diode (JEDEC method)	I_{FSM}	120					A
Junction Capacitance (Note1)	C_J	700		300			pF
Storage Temperature Range	T_{STG}	-55 to +150					°C
Operation Temperature Range	T_J	-55 to +150					°C

ELECTRONICAL CHARACTERISTICS

Parameter	Symbol	MBR1045 LCT	MBR1060 LCT	MBR10100 LCT	MBR10150 LCT	MBR10200 LCT	units
Maximum Forward Voltage Drop per diode at 5A (Note 2)	V_F	0.55	0.65	0.80	0.85	0.90	V
Maximum DC Reverse Current at rated DC blocking voltage (Note 2)	@ $T_C=25^\circ\text{C}$	0.15			0.1		mA
	@ $T_C=100^\circ\text{C}$	40.0			20.0		

THERMAL CHARACTERISTICS

Parameter	Symbol	ITO-220	TO-220	TO-262 TO-263	units
Typical Thermal Resistance (Note 3)	$R_{th(jc)}$	3.5	2.5	2.5	°C/W

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc.
2. Pulse test: 300 μs pulse width, 1% duty cycle.
3. Thermal Resistance from Junction to Case Mounted on heatsink.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [pingwei manufacturer](#):

Other Similar products are found below :

[KBJ1008](#) [SB5150L](#) [P6SMBJ68CA](#) [GBU410](#) [DB207S](#) [KBJ1006](#) [SB5P45](#) [KBJ1010](#) [GBL410](#) [GBU408](#) [PS40U60CT](#) [MBR20200CT](#) [D16-](#)
[DSS16](#) [MUR1040CT](#) [MBR30100CT](#) [MBR20200FCT](#) [MBR20100CT](#) [MBR20150FCT](#) [FR107](#) [GBU806](#) [HBRA10100BCT](#) [SB2200](#)
[MUR1620CTR](#) [SB5150](#) [GBU1006](#) [1N5404](#) [6A2](#) [PS10U100S](#) [GS1G](#) [GBJ2010](#) [GBU606](#) [16N65MF](#) [20N65NF](#) [HER303](#) [6A1](#) [1N5395](#)
[SF16](#) [18N50MF](#) [MBR30100FCT](#) [MUR1640FCT](#) [MBR30200FCT](#) [SS510B](#) [GBU406](#) [GBP206](#) [KBJ406](#) [100N10NF](#) [MBR10200FCT](#)
[GBU808](#) [SS3T10A](#) [PS40U100CT](#)